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23 35 (((fabricat\$3 with gan with substrate) and (crack or fault or defect)) and (buffer with gan)) and ((buffer with first) and (buffer with second)) 24 3 ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with gan))) and ((((fabricat\$3 with gan with substrate) and (crack or fault or defect)) and (buffer with gan)) and ((buffer with first) and (buffer with second))) 25 566 ((sapphire with substrate) and (crack or fault or defect)) and (buffer with (multi adj layer) or (multiple adj layer))) 26 ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with gan))) and ((buffer with dop\$3 with buffer) or (silicon with dop\$3 with gan))) and ((buffer with (multi adj layer))) 27 ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with gan))) and ((buffer with (multi adj layer))))
(crack or fault or defect)) and (buffer with gan)) and ((buffer with first) and (buffer with second)) (sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with substrate) and (crack or gan))) and (((fabricat\$3 with gan with substrate) and (buffer with first) and (buffer with second))) (buffer with ((multi adj layer))) (csapphire with substrate) and (crack or fault or defect)) and (buffer with second))) (csapphire with substrate) and (crack or fault or defect) and (crack or fault or defect)) (crack or fault first) and (crack or fault or defect)) (csapphire with gan) and (buffer with first) and (buffer with second)) (csapphire with gan) and (crack or fault or defect) (crack or fault or defect) and (condition with dop\$3 with gan))) and (condition with dop\$3 with gan)) and (condition with dop\$3 with gan) and gan
with gan)) and ((buffer with first) and (buffer with second)) ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with gan))) and (((fabricat\$3 with gan with substrate) and (buffer with gan)) and ((buffer with first) and (buffer with second))) (buffer with ((multi adj layer))) ((sapphire with substrate) and (crack or fault or defect)) and (buffer with second))) ((sapphire with substrate) and (crack or (multiple adj layer))) ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with layer)) ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with layer))) ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with layer))) ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with layer))) ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with layer))) ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with layer)))
(buffer with second)) ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with substrate) and (crack or fault or defect)) and (((fabricat\$3 with gan with substrate) and (buffer with first) and (buffer with second))) (buffer with ((multi adj layer) or (multiple adj layer))) ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with buffer) or (silicon with dop\$3 with layer) or (multiple adj layer))) ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with layer) or (multiple adj layer)))
24 3 ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with substrate) and (((fabricat\$3 with gan with substrate) and (crack or fault or defect)) and (buffer with gan)) and ((buffer with first) and (buffer with second))) 25 566 ((sapphire with substrate) and (crack or (multiple adj layer))) 26 ((sapphire with substrate) and (crack or fault or defect) and (silicon with dop\$3 with buffer) or (silicon with dop\$3 with layer) or (multiple adj layer))) 26 (sapphire with substrate) and (crack or fault or defect) and (silicon with dop\$3 with layer) or (multiple adj layer)))
fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with gan))) and ((((fabricat\$3 with gan with substrate) and (crack or fault or defect)) and (buffer with gan)) and ((buffer with first) and (buffer with second))) (buffer with ((multi adj layer) or (multiple adj layer))) 566 ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with layer) or (multiple adj layer))) ((sapphire with ((multi adj layer)))) ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with layer) or (multiple adj layer)))) DERWENT 2003/06/13 17: DERWENT DERWENT
gan)) and ((((fabricat\$3 with gan with substrate) and (crack or fault or defect)) and (buffer with gan)) and ((buffer with first) and (buffer with second))) (buffer with ((multi adj layer) or (multiple adj layer))) 566 ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with buffer) or (silicon with dop\$3 with layer) or (multiple adj layer))) DERWENT 2003/06/13 18: US-PGPUB; EPO; JPO; DERWENT 2003/06/13 17: DERWENT
substrate) and (crack or fault or defect)) and (buffer with gan)) and ((buffer with first) and (buffer with second))) (buffer with ((multi adj layer) or (multiple adj layer))) 566 ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with gan))) and ((buffer with ((multi adj layer) or (multiple adj layer)))) USPAT; US-PGPUB; EPO; JPO; DERWENT 2003/06/13 17: DERWENT
and (buffer with gan)) and ((buffer with first) and (buffer with second))) (buffer with ((multi adj layer) or (multiple adj layer))) 5 ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with gan))) and ((buffer with ((multi adj layer)))) 2003/06/13 18: 2003/06/13 17: 2003/06/13 17: 2003/06/13 17: DERWENT DERWENT
first) and (buffer with second))) (buffer with ((multi adj layer) or (multiple adj layer))) 5 ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with gan))) and ((buffer with ((multi adj layer) or (multiple adj layer)))) 2003/06/13 18: 2003/06/13 18: 2003/06/13 17: 2003/06/13 17: 2003/06/13 17:
(buffer with ((multi adj layer) or (multiple adj layer))) ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with gan))) and ((buffer with ((multi adj layer)))) ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with gan))) and ((buffer with ((multi adj layer))))
(multiple adj layer))) 5 ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with gan))) and ((buffer with ((multi adj layer) or (multiple adj layer)))) US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; DERWENT DERWENT
5 ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with gan))) and ((buffer with ((multi adj layer) or (multiple adj layer)))) EPO; JPO; DERWENT US-PGPUB; EPO; JPO; DERWENT
26 ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with with buffer) or (silicon with dop\$3 with gan))) and ((buffer with ((multi adj layer) or (multiple adj layer))))
fault or defect) and ((silicon with dop\$3 US-PGPUB; with buffer) or (silicon with dop\$3 with gan))) and ((buffer with ((multi adj DERWENT layer) or (multiple adj layer))))
with buffer) or (silicon with dop\$3 with EPO; JPO; gan))) and ((buffer with ((multi adj DERWENT layer) or (multiple adj layer))))
gan))) and ((buffer with ((multi adj DERWENT layer) or (multiple adj layer))))
layer) or (multiple adj layer))))
131 - AJ FONDELDE MILL COMPLET OF LOSTOTE FOR A 1500 A 20 TO
25 (buffer with ((multi adj layer) or USPAT; 2003/06/13 1/. (multiple adj layer)) with dop\$3) US-PGPUB;
EPO; JPO;
DERWENT
28 19 ((buffer with ((multi adj layer) or USPAT; 2003/06/13 17:
(multiple adj layer)) with dop\$3)) and US-PGPUB;
@ad<20010305 EPO; JPO;
DERWENT 2 (gap with semiconductor with substrate USPAT; 2003/06/13 17:
2 (gair with Semiconductor with Substitute state
yith fabrication) and ((buffer with US-PGPUB; (multi adj layer) or (multiple adj EPO; JPO;

				0002/06/12 17:12
30	42	((buffer with ((multi adj layer) or	USPAT;	2003/06/13 17:13
		(multiple adj layer)))) and gan and	US-PGPUB; EPO; JPO;	
		sapphire	DERWENT	
		tion consists (imple) and layor) or	USPAT;	2003/06/13 18:57
31	27	(((buffer with ((multi adj layer) or	US-PGPUB;	
		(multiple adj layer)))) and gan and sapphire) and @ad<20010305	EPO; JPO;	
		sapphire, and ead 20010303	DERWENT	
22	0	((buffer with ((multi adj layer) or	USPAT;	2003/06/13 17:58
32	Ĭ	(multiple adj layer))) same gradient same	US-PGPUB;	
	ļ	dop\$3) and gan	EPO; JPO;	
]		DERWENT	0000 (05 (10 17 50
33	0	((buffer same ((multi adj layer) or	USPAT;	2003/06/13 17:58
		(multiple adj layer))) same gradient same	US-PGPUB;	
		dop\$3) and gan	EPO; JPO;	
] 		DERWENT USPAT;	2003/06/13 17:59
34	0	((buffer same ((multi adj layer) or	US-PGPUB;	2003/00/13 17.03
		(multiple adj layer))) same gradient) and	EPO; JPO;	
		gan	DERWENT	
	7	buffer same gan same gradient	USPAT;	2003/06/13 18:05
35	1 '	buller same gan same gradrene	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
36	148	(buffer same gradient) and gan	USPAT;	2003/06/13 18:24
			US-PGPUB;	
			EPO; JPO;	1
			DERWENT	2003/06/13 18:05
37	0	((buffer with ((multi adj layer) or	USPAT; US-PGPUB;	2003/00/13 10:03
		(multiple adj layer)) with dop\$3)) and	EPO; JPO;	
		((buffer same gradient) and gan)	DERWENT	
		((buffer with ((multi adj layer) or	USPAT;	2003/06/13 18:05
38		(multiple adj layer)))) and ((buffer same	US-PGPUB;	
		gradient) and gan)	EPO; JPO;	
		gradiency and gam,	DERWENT	
39	3	(buffer with ((multi adj layer) or	USPAT;	2003/06/13 18:23
		(multiple adj layer))) and (buffer same	US-PGPUB;	
į		concentration same gradient)	EPO; JPO;	
			DERWENT USPAT;	2003/06/13 18:49
40	213	buffer with layer with gradient	US-PGPUB;	2003/00/23 20:15
			EPO; JPO;	
			DERWENT	
4.3	12	(buffer with layer with gradient) and gan	USPAT;	2003/06/13 18:49
41	12	(Bullet with injury)	US-PGPUB;	
j			EPO; JPO;	1
			DERWENT	0000/06/10 10:40
42	5	buffer with (dichlorosilane or	USPAT;	2003/06/13 18:43
		"sih.sub.2cl.sub.2")	US-PGPUB;	
			EPO; JPO;	
			DERWENT USPAT;	2003/06/13 18:49
43	531	(buffer with layer) same gradient	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
	22	((buffer with layer) same gradient) and	USPAT;	2003/06/13 18:57
44	1	gan	US-PGPUB;	
		3	EPO; JPO;	
			DERWENT	0000/06/10 10 55
45	209	super with lattice with dop\$3	USPAT;	2003/06/13 18:57
7			US-PGPUB;	
			EPO; JPO;	
			DERWENT USPAT;	2003/06/13 18:57
46	19	(super with lattice with dop\$3) same gan	US-PGPUB;	2000,00,10 10.0
			EPO; JPO;	
			DERWENT	
47	12	((super with lattice with dop\$3) same gan)	USPAT;	2003/06/13 19:09
" '	12	and @ad<20010305	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
			·	

10	1			
48	10	(((super with lattice with dop\$3) same gan) and @ad<20010305) and buffer	USPAT; US-PGPUB;	2003/06/13 19:07
	,		EPO; JPO; DERWENT	
49	44	(first adj buffer) and (second adj buffer)	USPAT;	2003/06/13 19:35
		and concentration and symmetrical	US-PGPUB;	2000,00,13 15.55
			EPO; JPO;	
50	20		DERWENT	
50	39	((first adj buffer) and (second adj	USPAT;	2003/06/13 20:09
		buffer) and concentration and symmetrical) and @ad<20010305	US-PGPUB;	
		and ead 20010303	EPO; JPO; DERWENT	
51	181	(first adj buffer) and (second adj buffer)	USPAT;	2003/06/13 19:37
		and concentration and gradient	US-PGPUB;	
			EPO; JPO;	
52	22	//Finat adi buffan) / / / /	DERWENT	
32	22	((first adj buffer) and (second adj buffer) and concentration and gradient)	USPAT;	2003/06/13 20:06
		and (438/\$3.ccls. or 257/\$3.ccls.)	US-PGPUB; EPO; JPO;	
			DERWENT	
53	526	(buffer with dop\$3 with concentration) and	USPAT;	2003/06/13 20:21
		(438/\$3.ccls. or 257/\$3.ccls.)	US-PGPUB;	
			EPO; JPO;	
54	66	(/buffer with dones with concertantian)	DERWENT	0000/06/10 00 00
54		((buffer with dop\$3 with concentration) and (438/\$3.ccls. or 257/\$3.ccls.)) and	USPAT; US-PGPUB;	2003/06/13 20:08
		(buffer with multi\$3)	EPO; JPO;	
			DERWENT	
55	66	((buffer with dop\$3 with concentration)	USPAT;	2003/06/13 20:21
		and (438/\$3.ccls. or 257/\$3.ccls.)) and	US-PGPUB;	
		(buffer with multi\$3 with layer)	EPO; JPO;	
56	53	///buffer with dence with concentration	DERWENT	2002/06/12 20 50
30] 33	(((buffer with dop\$3 with concentration) and (438/\$3.ccls. or 257/\$3.ccls.)) and	USPAT; US-PGPUB;	2003/06/13 20:52
	İ	(buffer with multi\$3 with layer)) and	EPO; JPO;	
		@ad<20010305	DERWENT	
57	89	method with fabricat\$3 with gan with	USPAT;	2003/06/13 20:16
		substrate	US-PGPUB;	
	Ì		EPO; JPO;	
58	5	((buffer with dop\$3 with concentration)	DERWENT USPAT;	2003/06/13 20:16
30		and (438/\$3.ccls. or 257/\$3.ccls.)) and	US-PGPUB;	2003/06/13 20:16
		(method with fabricat\$3 with gan with	EPO; JPO;	
		substrate)	DERWENT	
59	12	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2003/06/13 20:39
		same (buffer with multiple with layer)	US-PGPUB;	
			EPO; JPO;	,
60	0	(buffer with dop\$3 with profile) same	DERWENT USPAT;	2003/06/13 20:38
		(buffer with multiple with layer)	US-PGPUB;	2003/00/13 20:38
		, a a a a a a a a a a a a a a a a a a a	EPO; JPO;	
			DERWENT	
61	2	(USPAT;	2003/06/13 20:40
		same (buffer with multiple with layer)	US-PGPUB;	
			EPO; JPO;	
62	4	(buffer with increas\$3 with dop\$3) same	DERWENT USPAT;	2003/06/13 20:42
	•	(buffer with multiple with layer)	US-PGPUB;	2003/00/13 20:42
			EPO; JPO;	
			DERWENT	
63	8	buffer with doping with concentration with	USPAT;	2003/06/13 20:45
		profile	US-PGPUB;	
			EPO; JPO;	
64	14	buffer with dop\$3 with gradient	DERWENT USPAT;	2003/06/13 20:51
	-	yawatiit	US-PGPUB;	2000,00,10 20.01
			EPO; JPO;	
	1000		DERWENT	
65	826	buffer with dop\$3 with concentration	USPAT;	2003/06/13 20:52
			US-PGPUB;	
<u> </u>			EPO; JPO; DERWENT	
			DELMENT	

66				
66	165	(buffer with dop\$3 with concentration) and	USPAT;	2003/06/13 20:52
		gan	US-PGPUB;	
			EPO; JPO;	
6.7			DERWENT	
67	45	1 transparent approximation concentration	USPAT;	2003/06/13 21:09
		and gan) and 438/\$3.ccls.	US-PGPUB;	2000,00,13 21.05
			EPO; JPO;	
			DERWENT	
68	31	(((buffer with dop\$3 with concentration)	USPAT;	2003/06/13 21:09
		and gan) and 438/\$3.ccls.) and	US-PGPUB;	2003/00/13 21.09
		@ad<20010305	EPO; JPO;	
	ļ		DERWENT	
69	89	buffer with doped with undoped with gan	USPAT;	2003/06/13 21:09
	1		US-PGPUB;	2003/00/13 21:09
			EPO; JPO;	
			DERWENT	ļ
70	61	(buffer with doped with undoped with gan)	USPAT;	2003/06/13 21:09
		and @ad<20010305	US-PGPUB;	2003/06/13 21:09
			EPO; JPO;	i
			DERWENT	
71	13	((buffer with doped with undoped with gan)	USPAT;	2002/06/12 21:00
		and @ad<20010305) and 438/\$3.ccls.	US-PGPUB;	2003/06/13 21:09
			EPO; JPO;	
	i i		DERWENT	
-	209	(fabricat\$3 with gan with substrate) and	USPAT;	2002/06/12 10:50
		(crack or fault or defect)	US-PGPUB;	2003/06/13 10:59
			EPO; JPO;	
			DERWENT]
-	147	((fabricat\$3 with gan with substrate) and	USPAT;	2002/06/12 15:20
		(crack or fault or defect)) and (buffer	US-PGPUB;	2003/06/13 15:39
		with gan)		
	1	- · · · · · · · · · · · · · · · · · · ·	EPO; JPO;]
-	17	((((fabricat\$3 with gan with substrate)	DERWENT	2002/06/12 15 40
]	and (crack or fault or defect)) and	USPAT;	2003/06/13 15:42
		(buffer with gan)) and ((buffer with	US-PGPUB;	
		first) and (buffer with second))) and	EPO; JPO;	
		@ad<20010305	DERWENT	
	<u> </u>			